



1/12

FIG. 1A

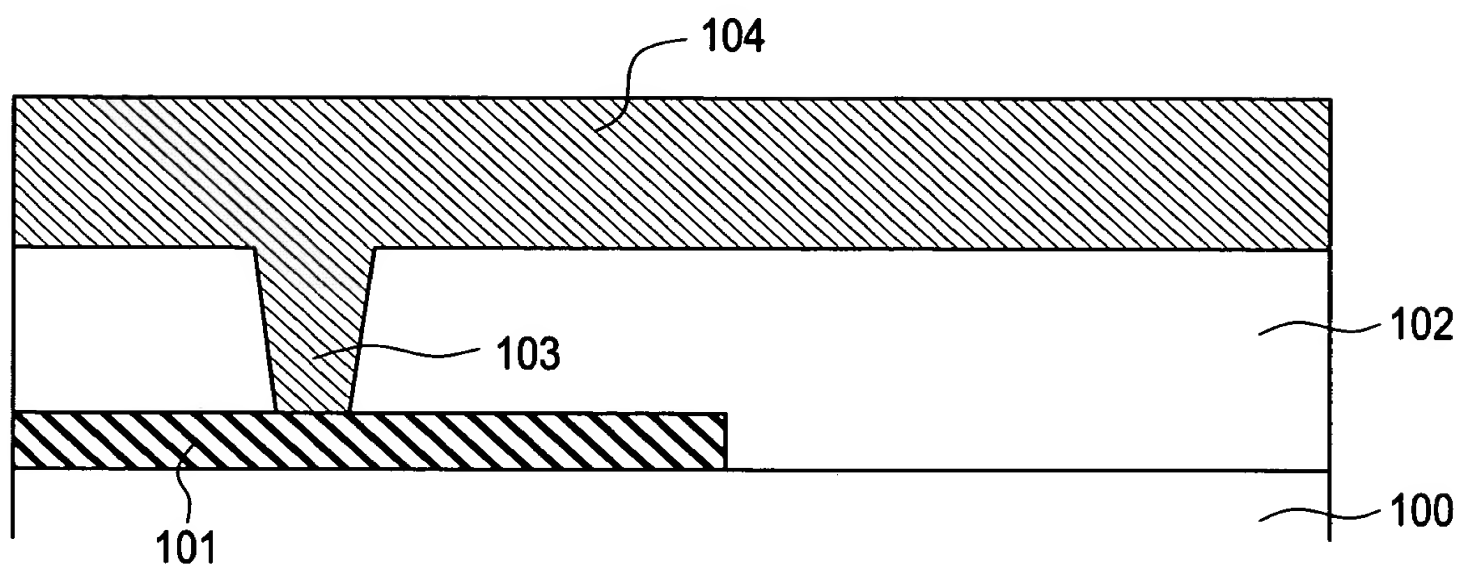


FIG. 1B

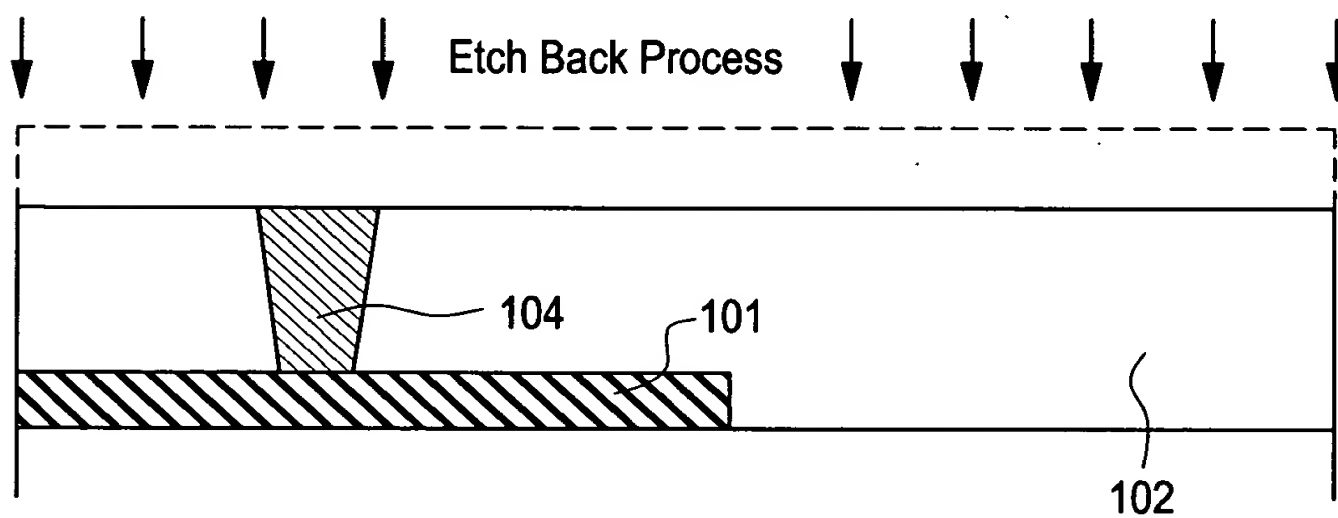


FIG. 1C

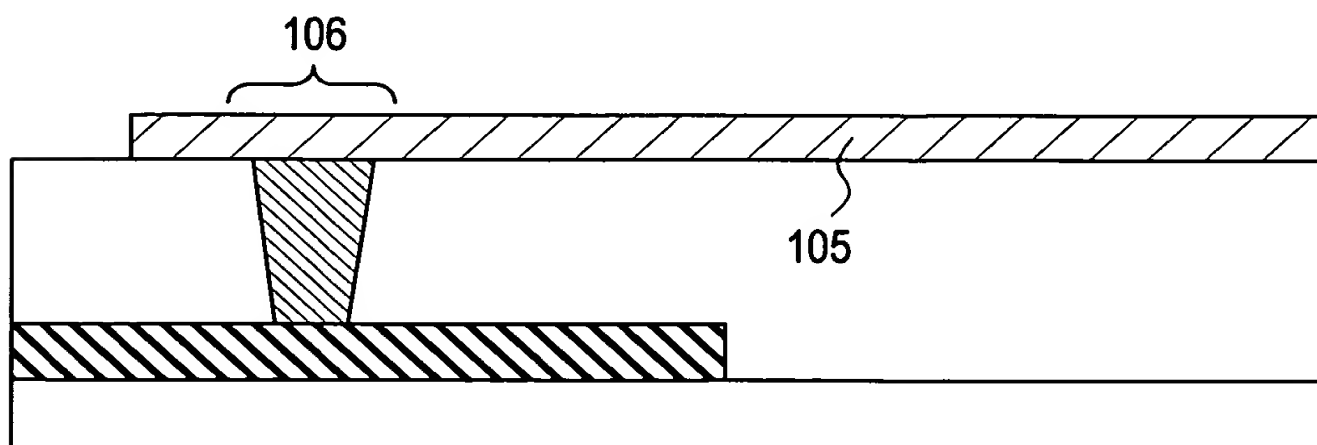


FIG. 2A

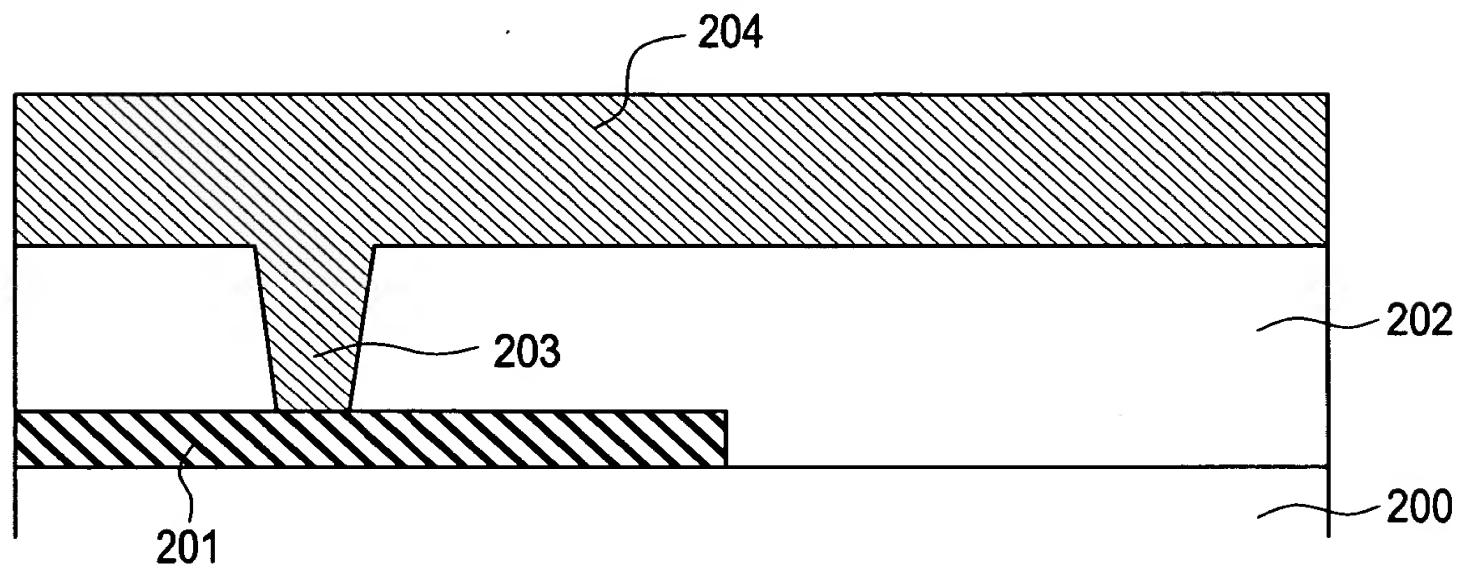


FIG. 2B

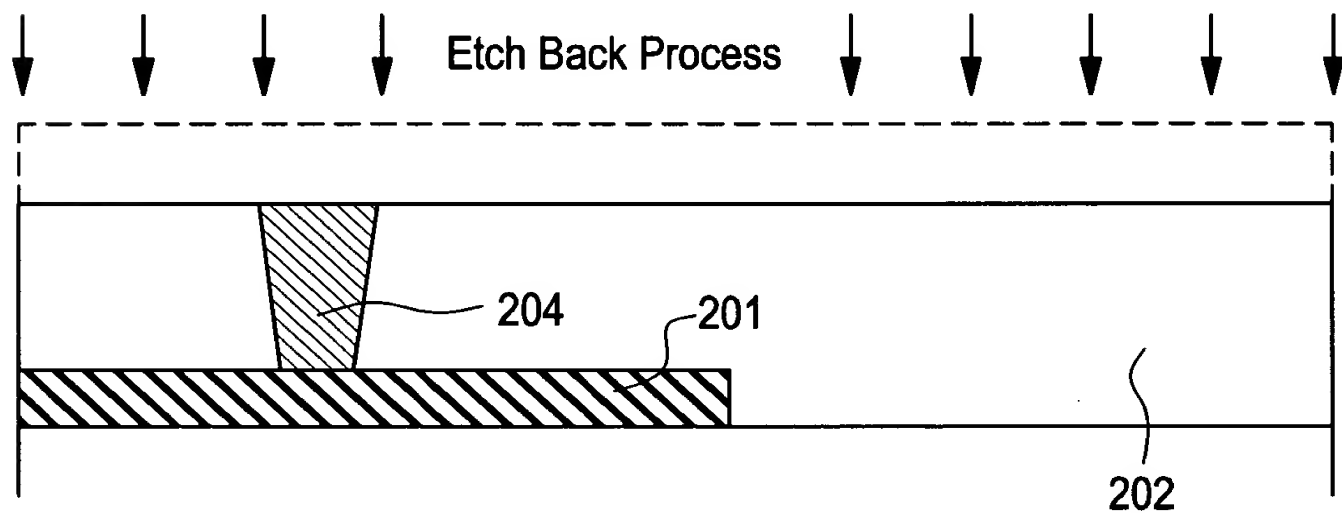


FIG. 2C

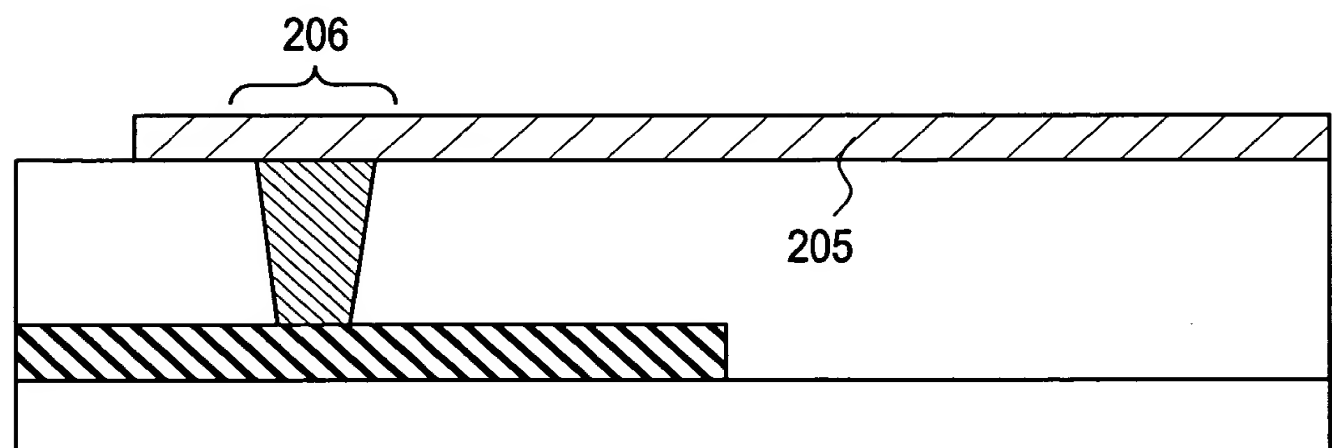


FIG. 3A

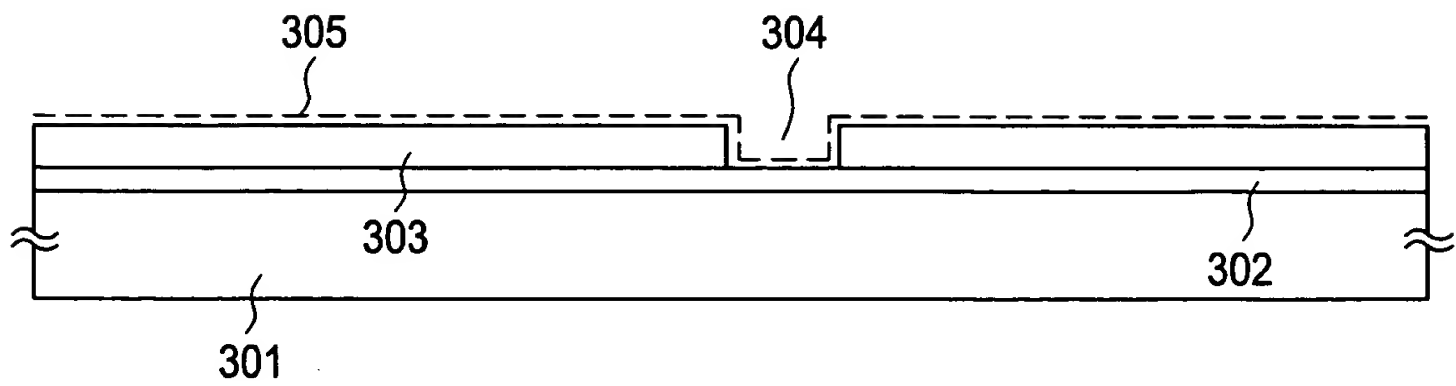


FIG. 3B

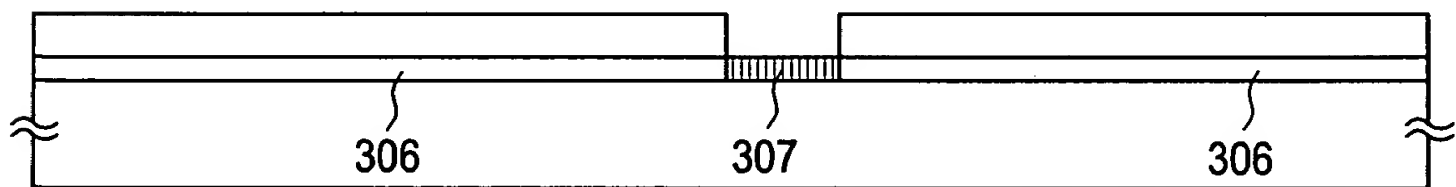


FIG. 3C

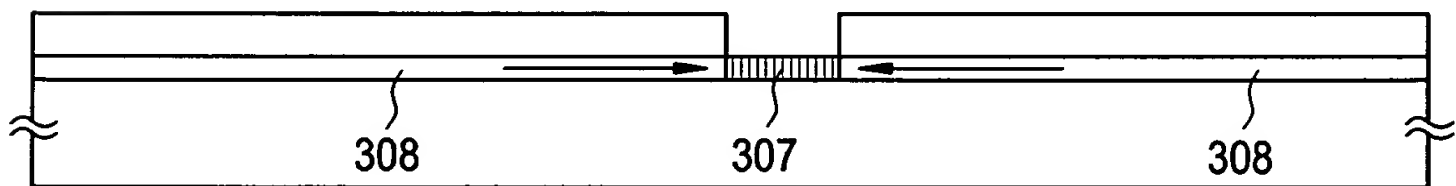


FIG. 3D

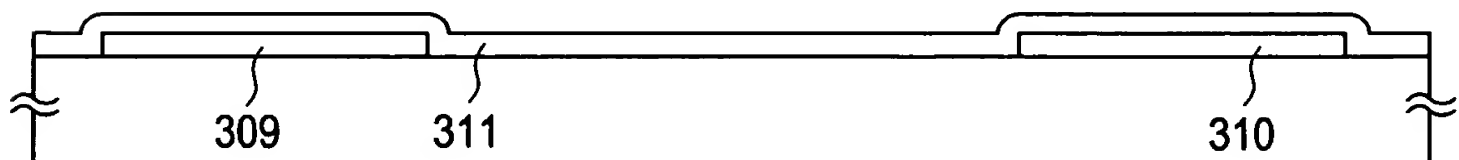


FIG. 4A

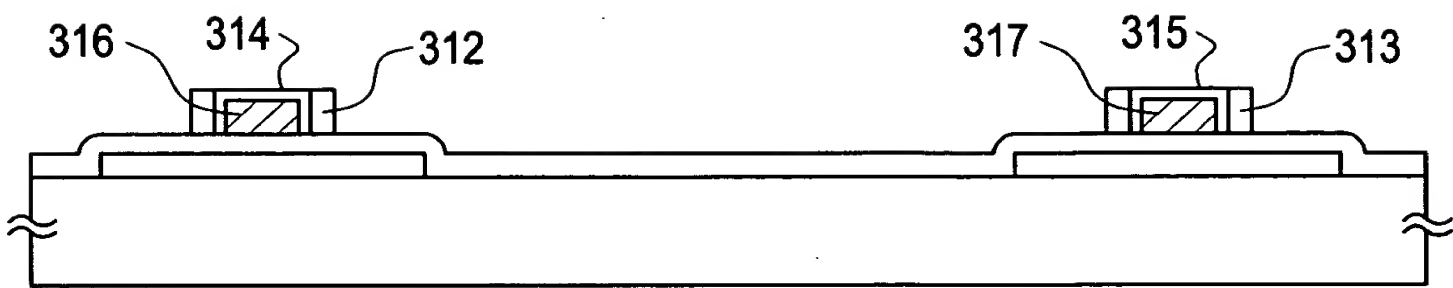


FIG. 4B

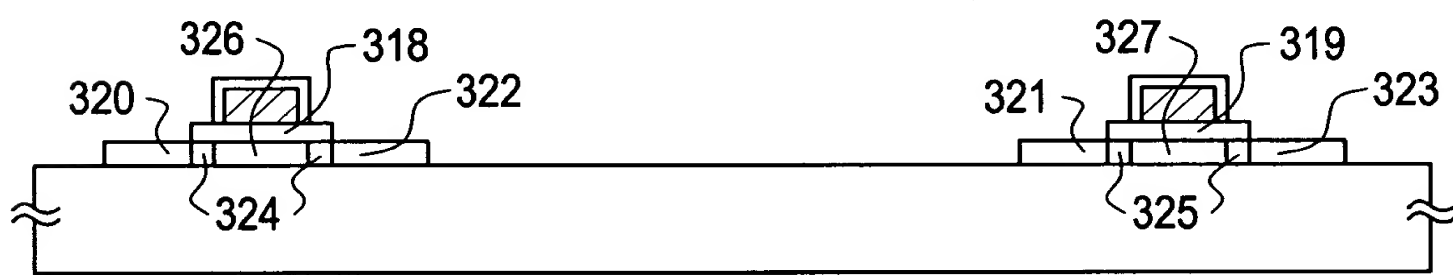


FIG. 4C

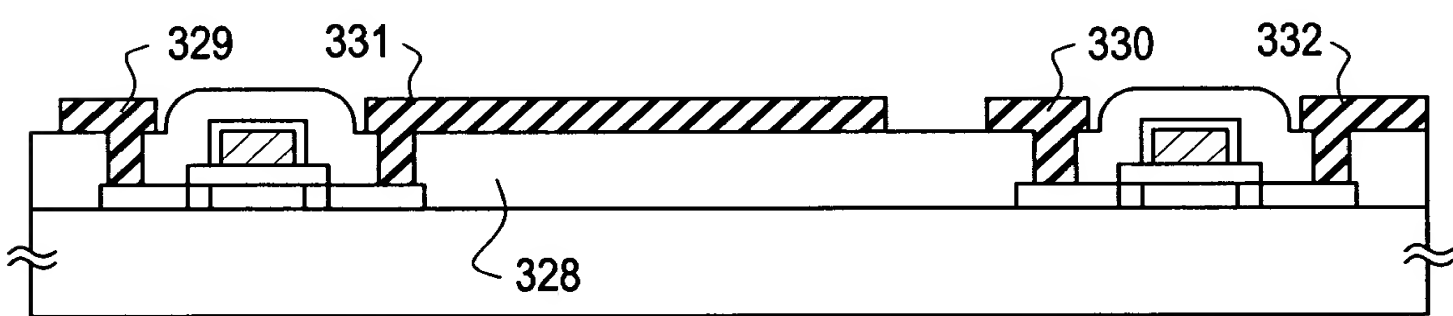


FIG. 4D

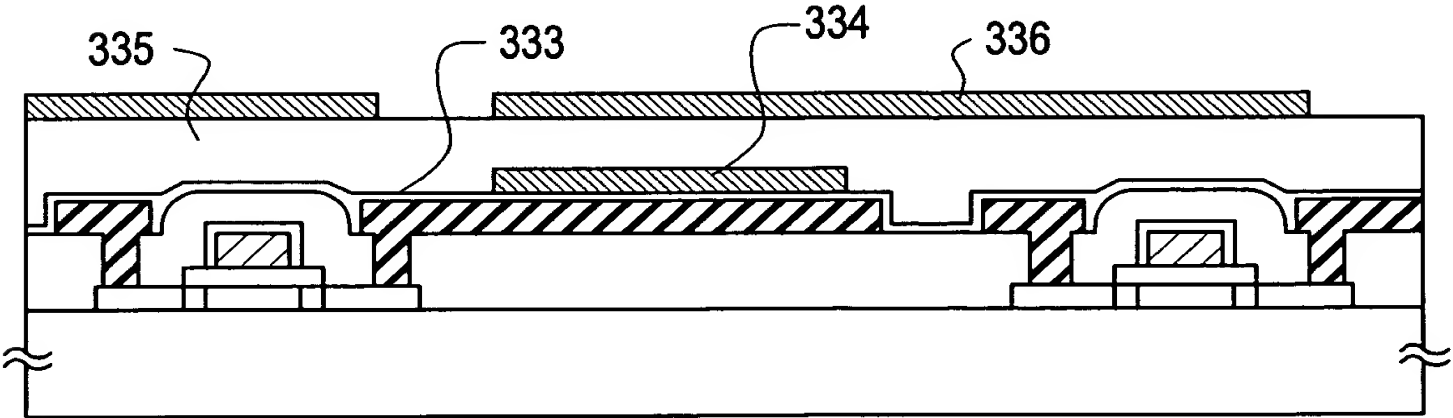


FIG. 5A

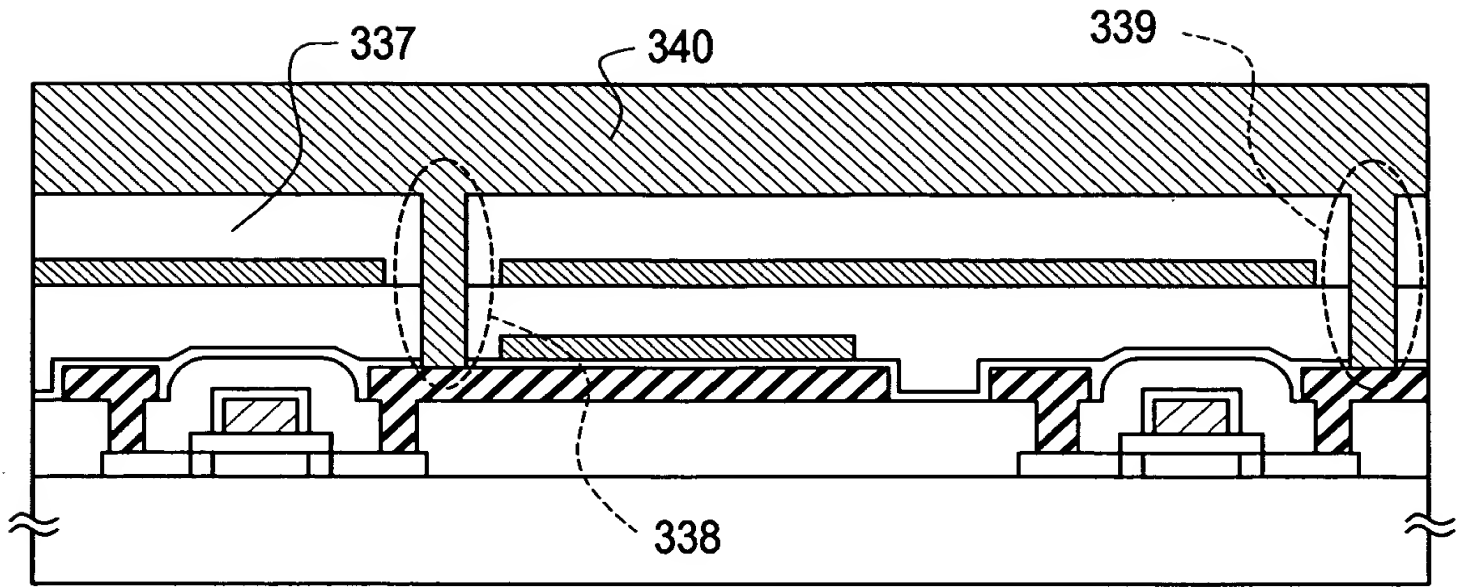


FIG. 5B

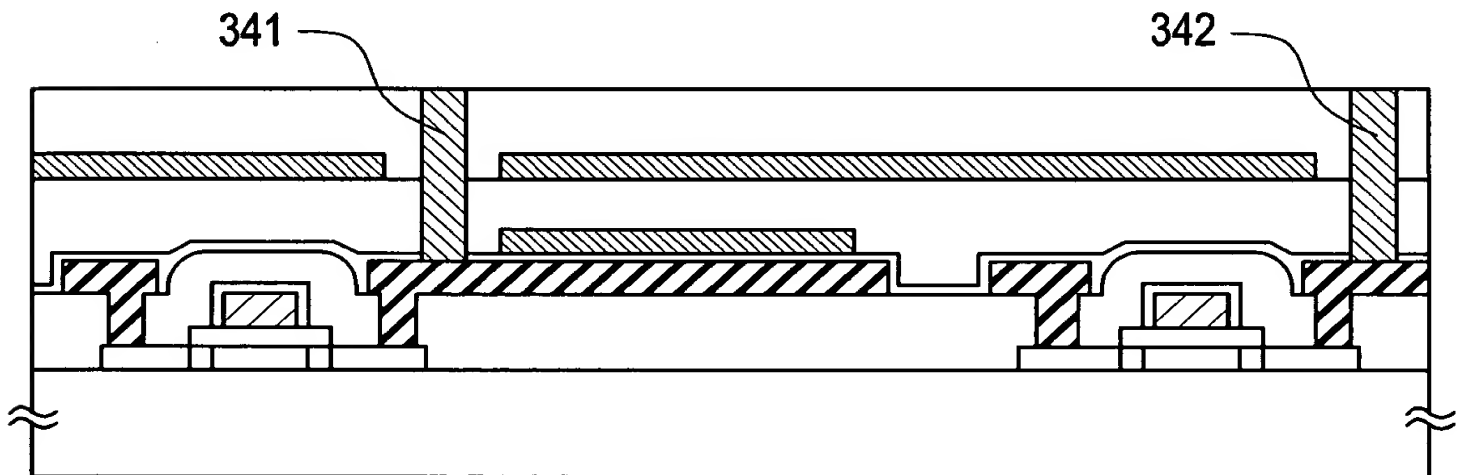


FIG. 5C

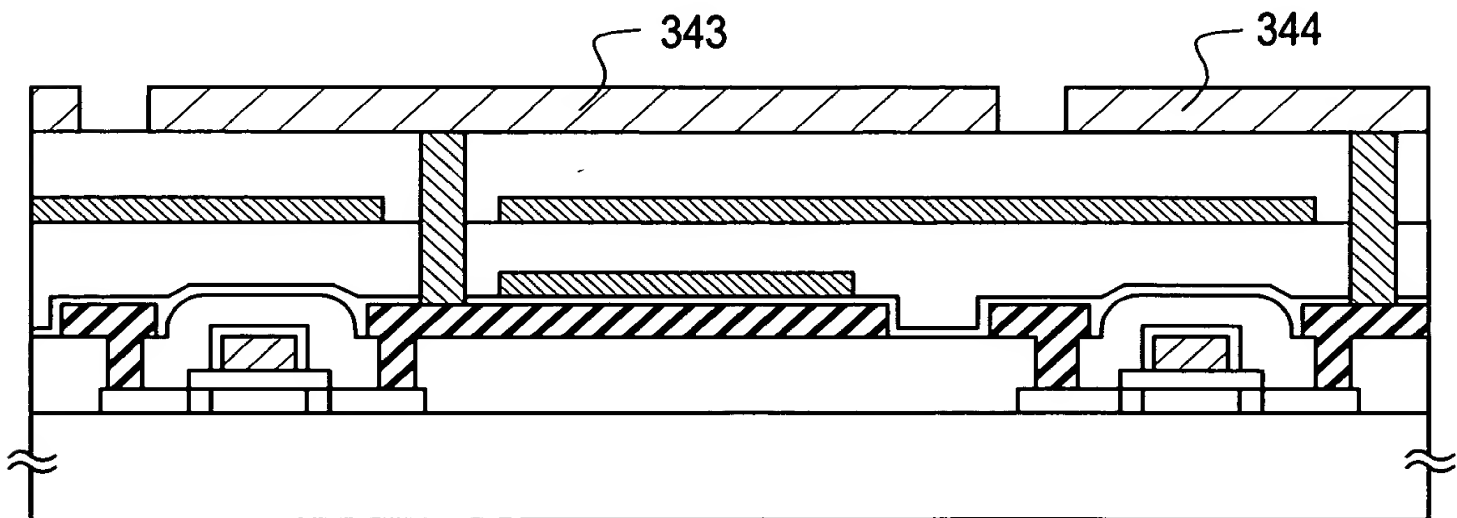


FIG. 6A

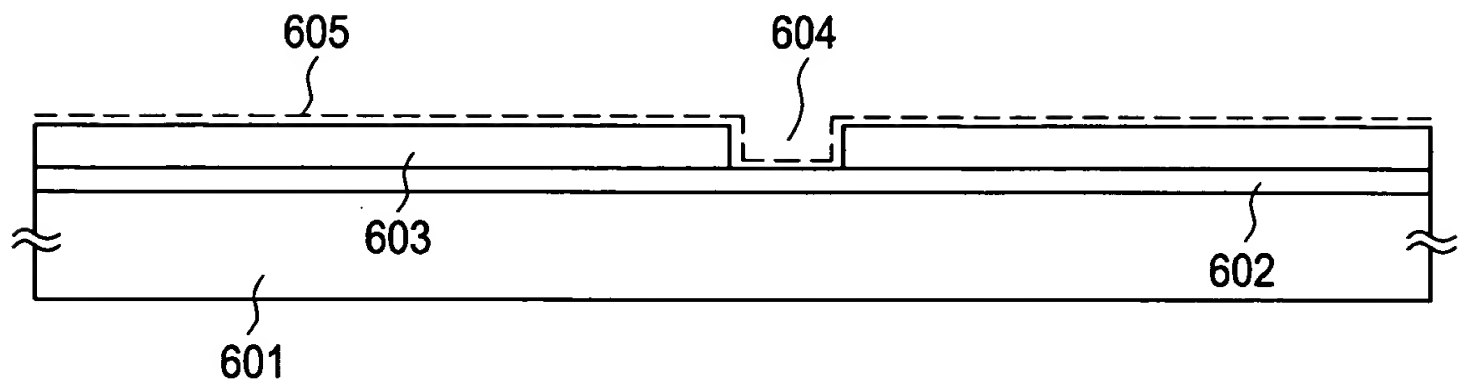


FIG. 6B

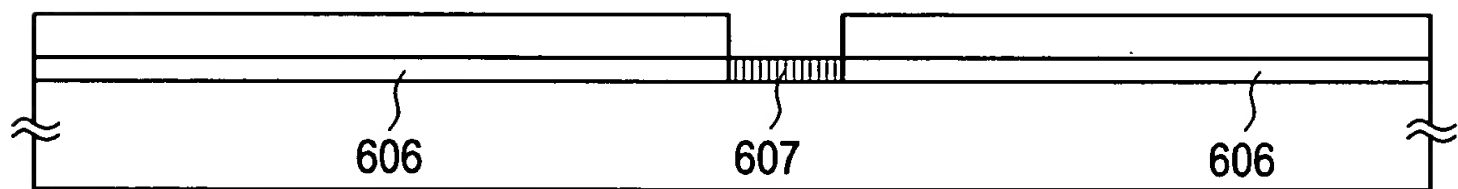


FIG. 6C

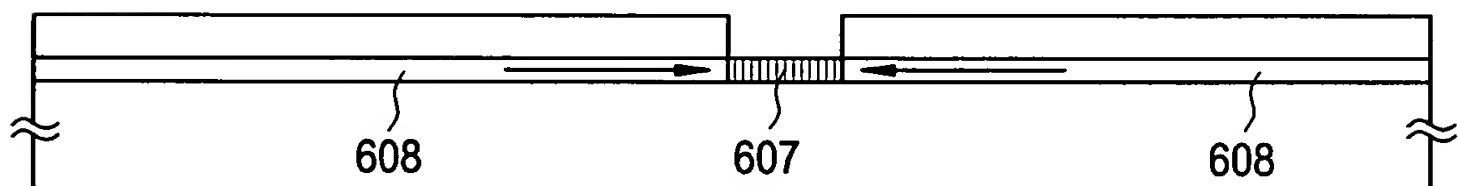


FIG. 6D

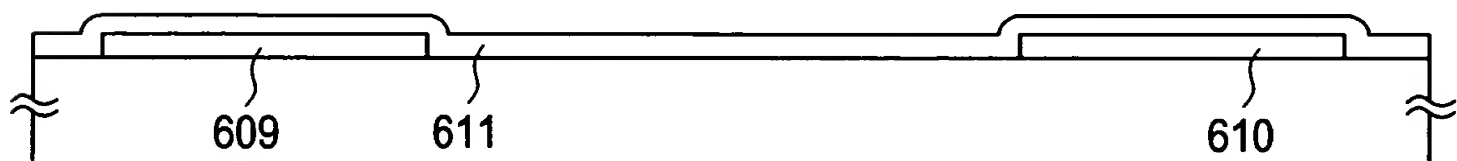


FIG. 7A

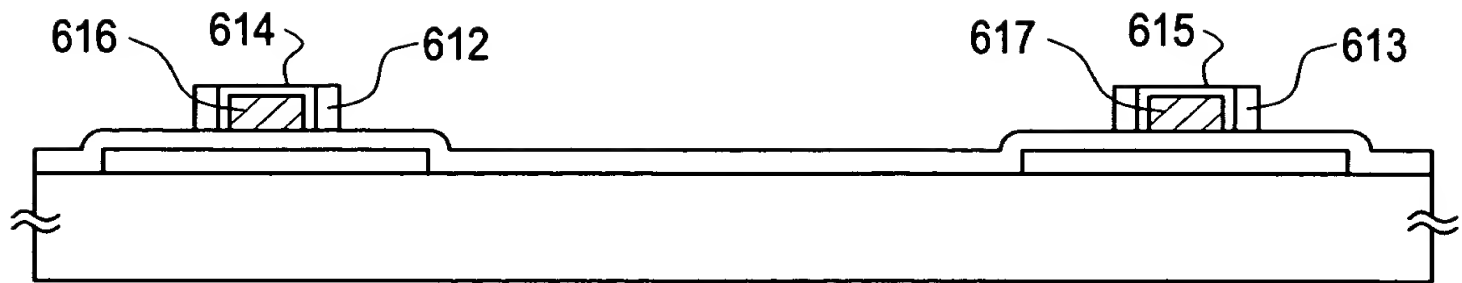


FIG. 7B



FIG. 7C

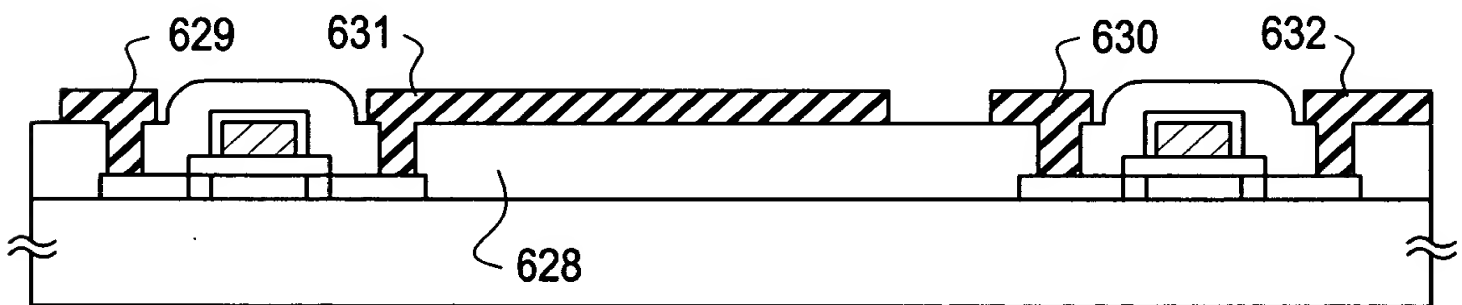


FIG. 7D

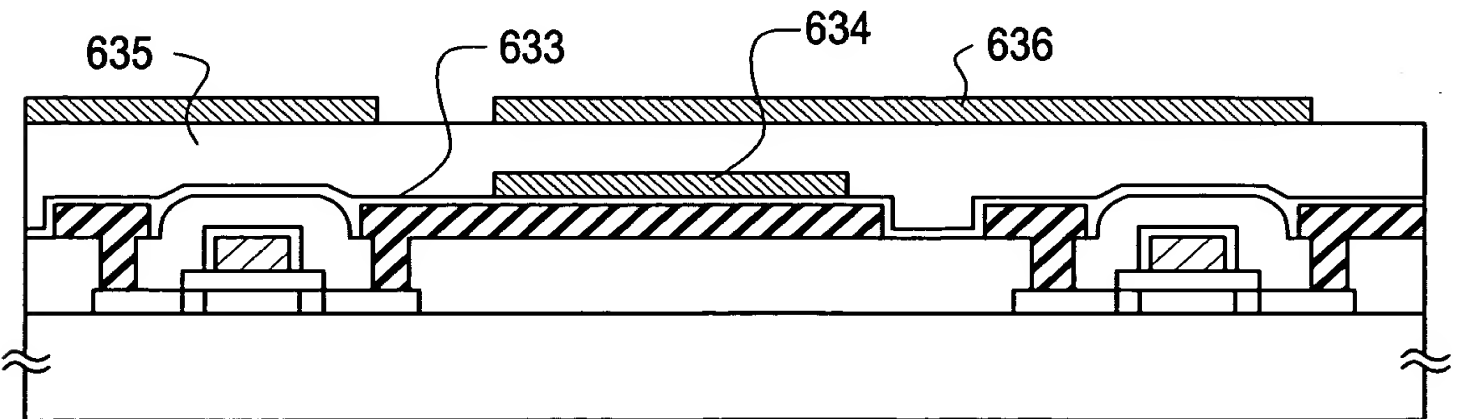


FIG. 8A

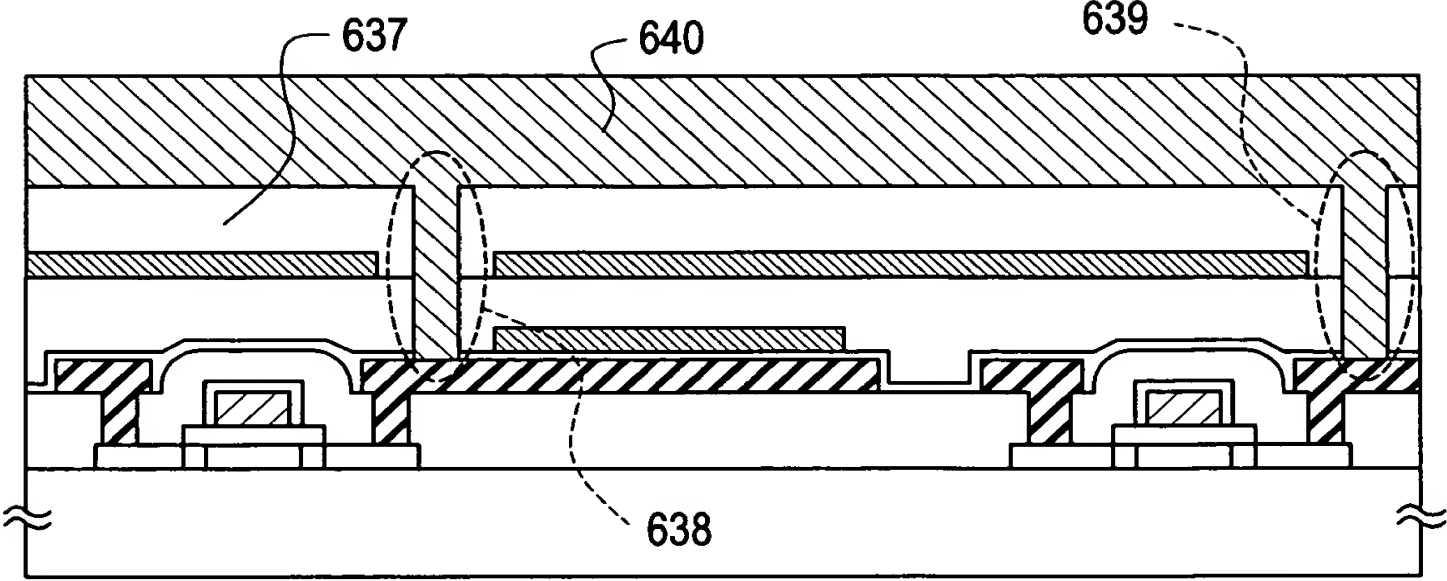


FIG. 8B

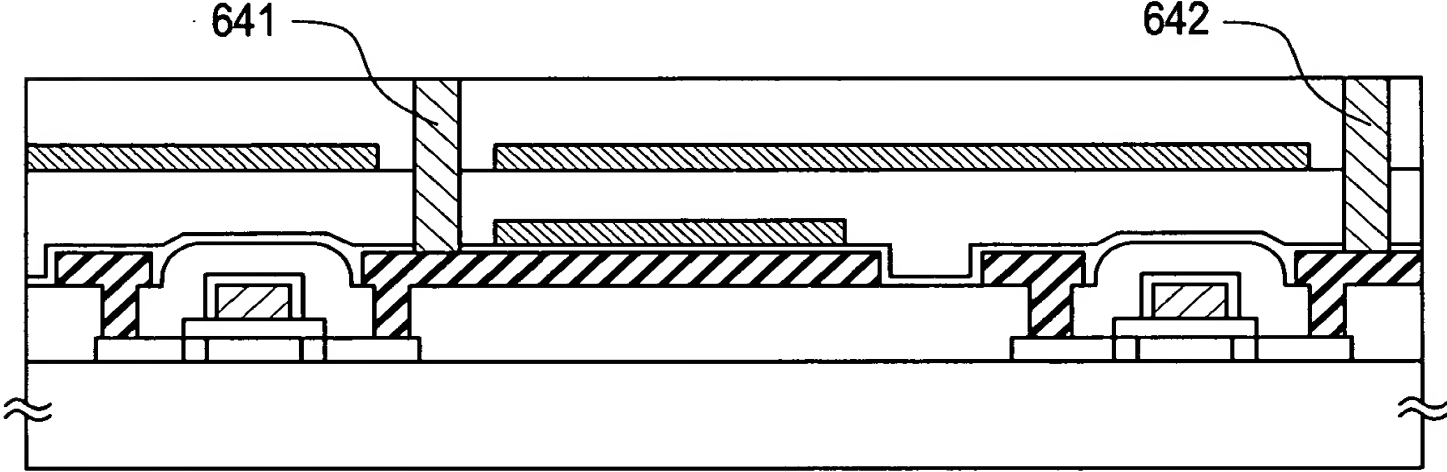
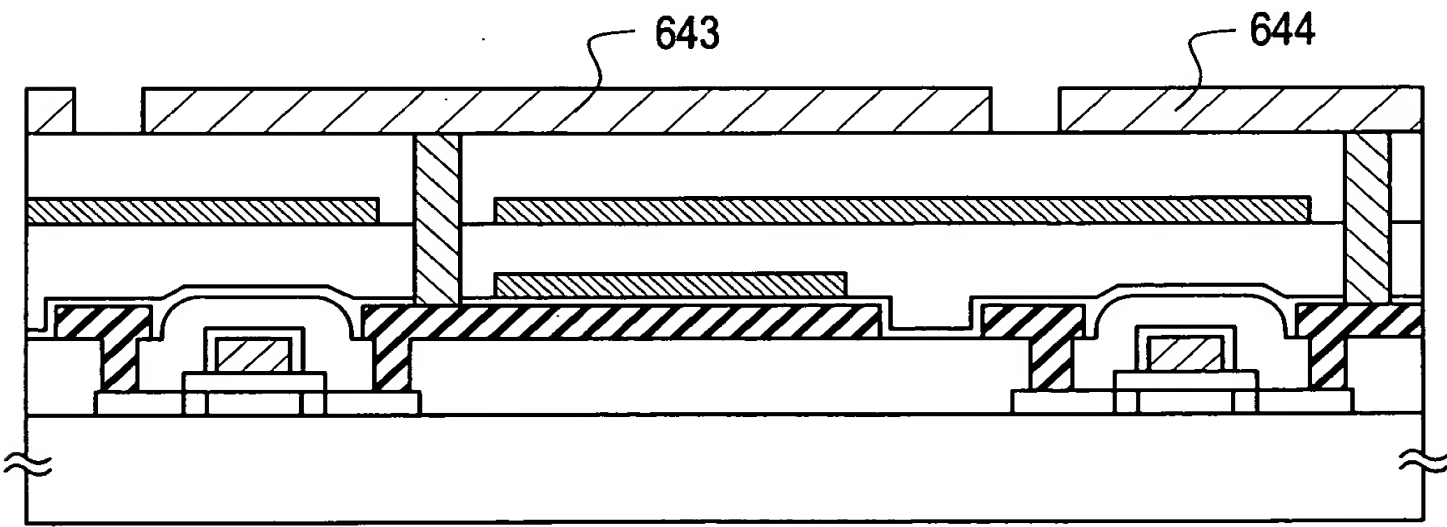


FIG. 8C





A cross-sectional view of a semiconductor device. The device features a central channel region (901) flanked by source/drain regions (902). Above the channel, there is a gate stack (903) and a contact layer (904). The device is built on a substrate with various layers and contacts, including a bottom gate and side contacts. The labels 901, 902, 903, and 904 point to specific structural components.

A cross-sectional view of a semiconductor device. The device features a central channel region 905 and side regions 906. The channel region 905 is defined by a central gate stack and is flanked by the side regions 906. The gate stack in the center consists of a gate dielectric, a gate electrode, and a gate spacer. The side regions 906 are defined by side gate stacks and are flanked by the channel region 905. The side gate stacks consist of a side gate dielectric, a side gate electrode, and a side gate spacer. The device is shown in a cross-sectional view with a central channel region 905 and side regions 906. The channel region 905 is defined by a central gate stack and is flanked by the side regions 906. The side gate stacks consist of a side gate dielectric, a side gate electrode, and a side gate spacer. The device is shown in a cross-sectional view with a central channel region 905 and side regions 906.

FIG. 10A

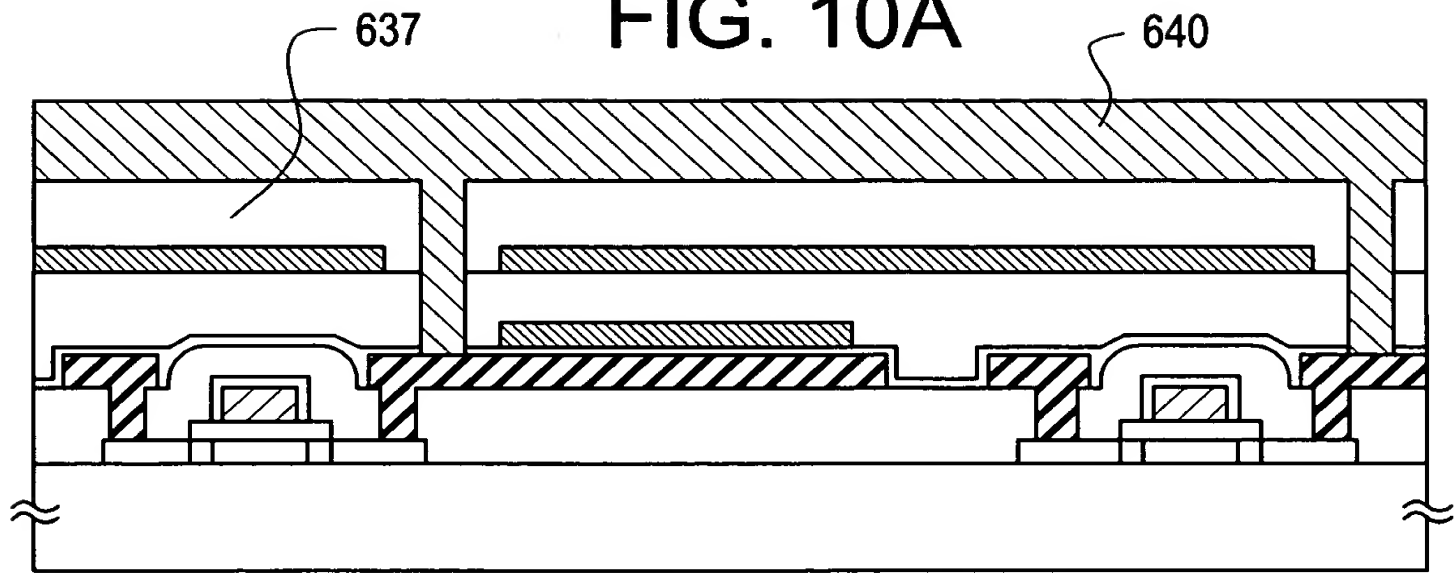


FIG. 10B

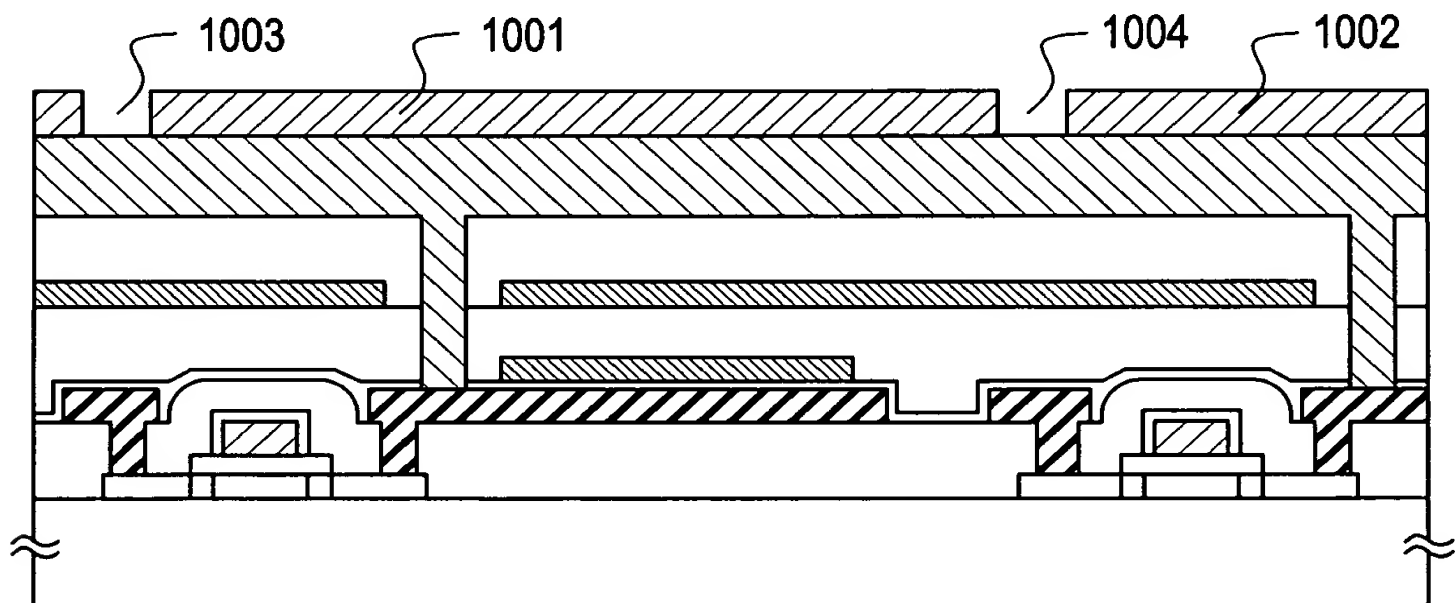


FIG. 10C

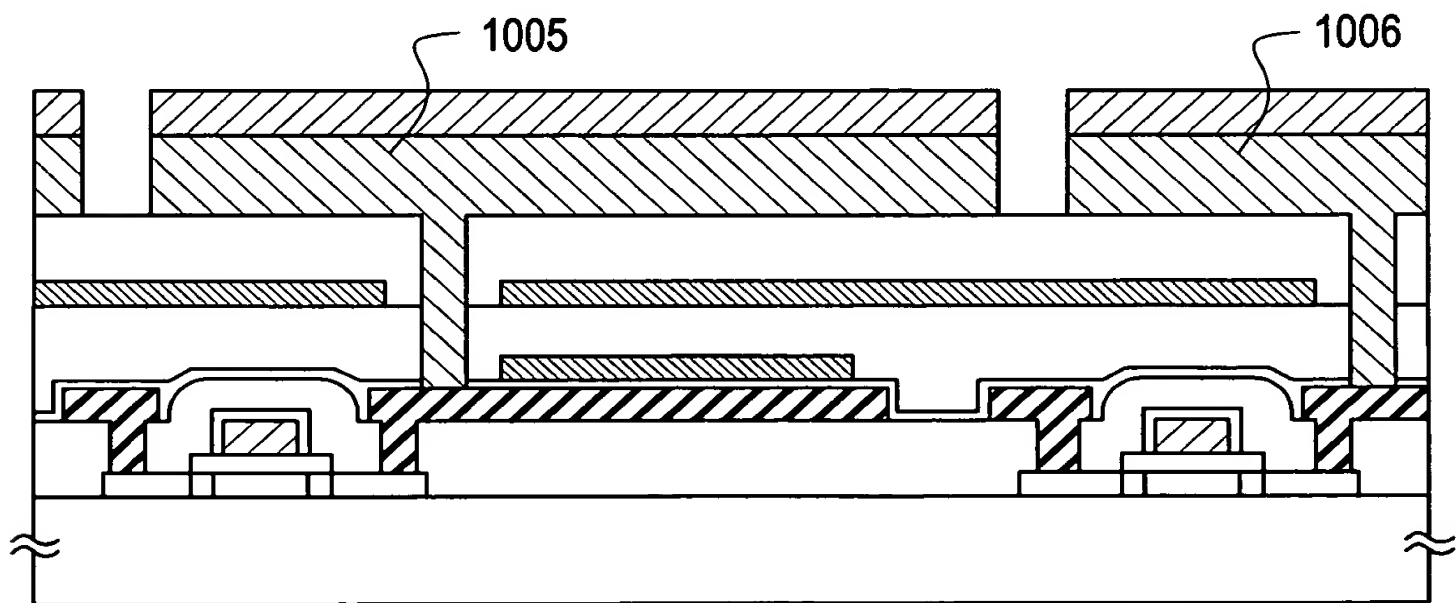


FIG. 11A

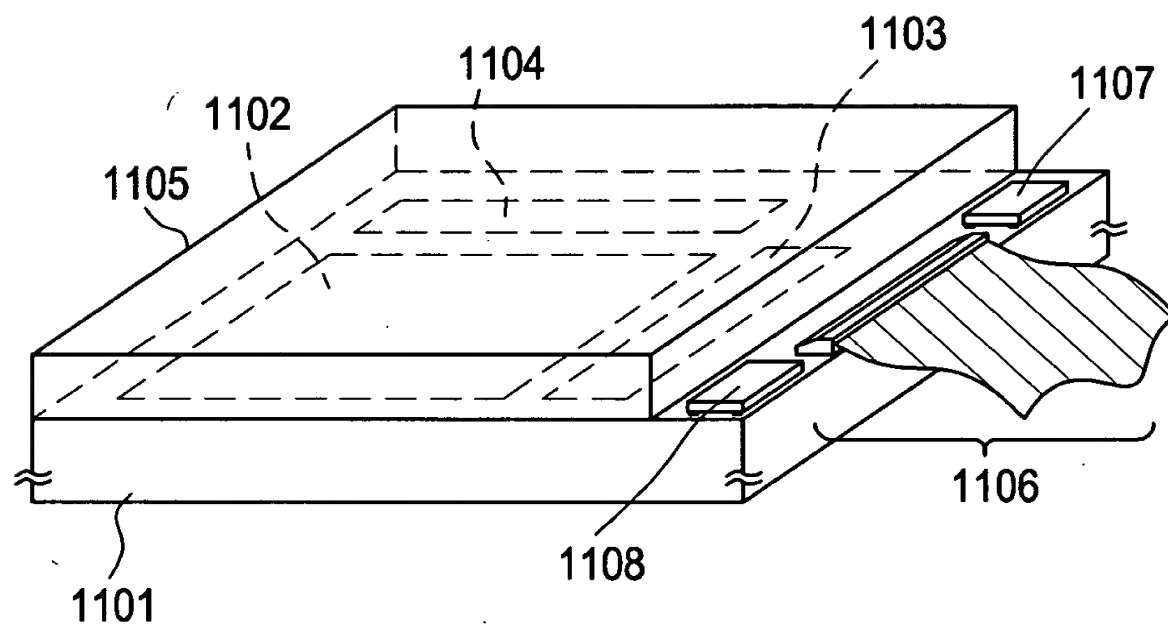


FIG. 11B

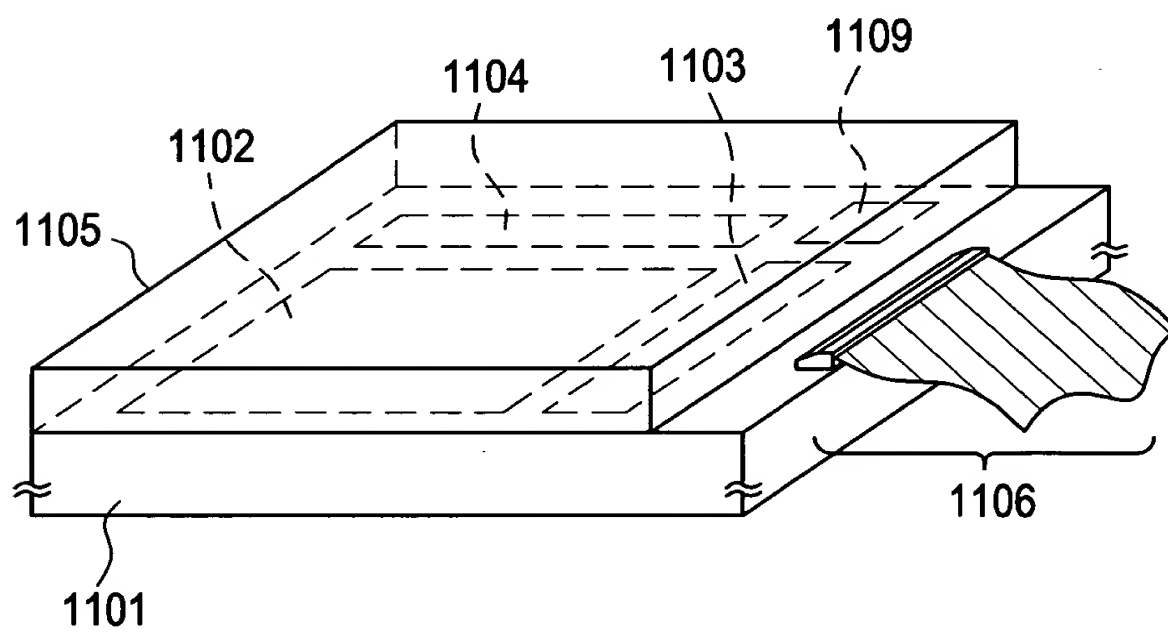


FIG. 12A

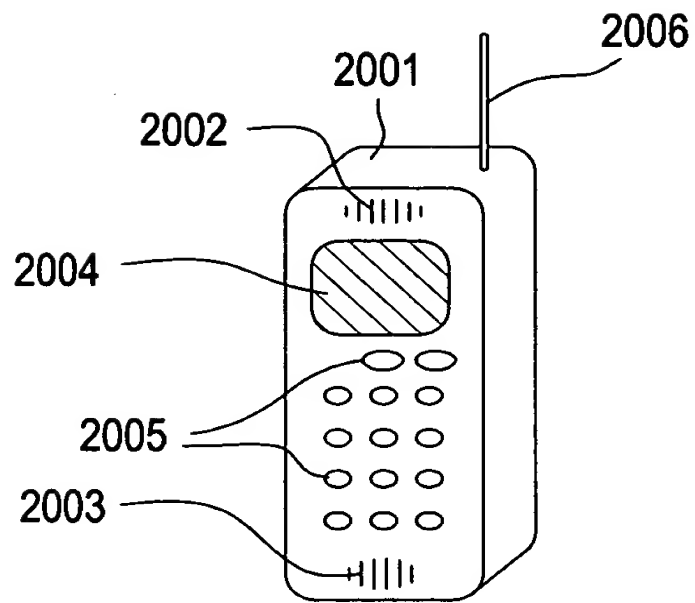


FIG. 12B

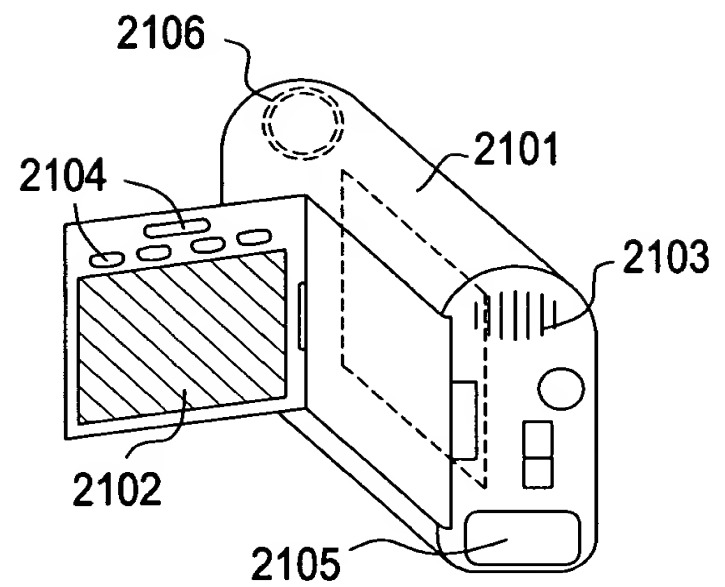


FIG. 12C

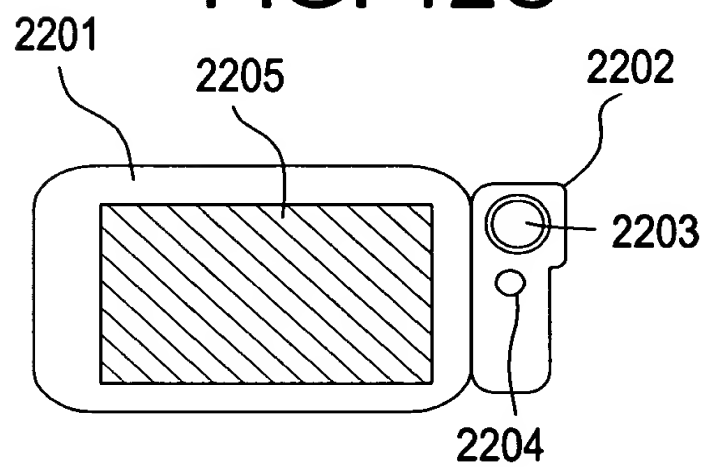


FIG. 12D

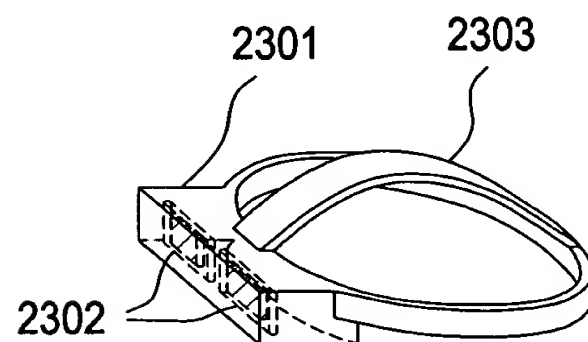


FIG. 12E

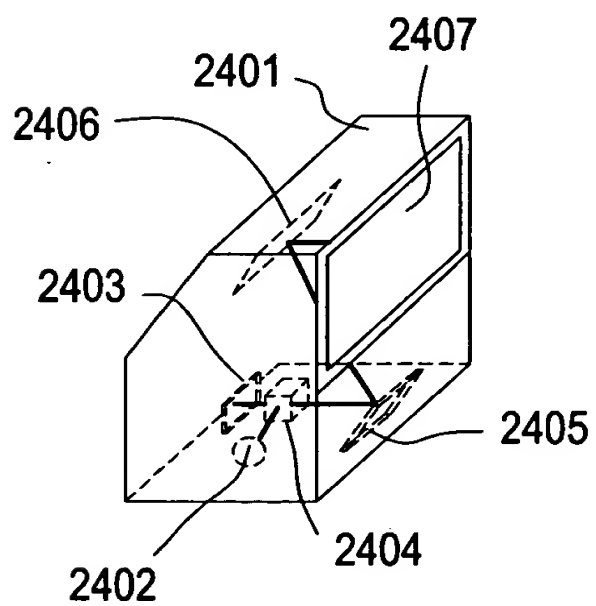


FIG. 12F

